

L Number	Hits	Search Text	DB	Time stamp
1	13740	semiconductor adj package	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:20
2	613	(semiconductor adj package) and (bonding adj pad)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:32
3	6	((semiconductor adj package) and (bonding adj pad)) and (polysilicon near layer) and thickness	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:30
4	19	((semiconductor adj package) and (bonding adj pad)) and (polysilicon)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:33
5	11	((semiconductor adj package) and (bonding adj pad)) and (polysilicon) and thickness	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:31
6	0	174/250-268 and (bonding adj pad)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:33
7	190	174/250-268.ccls. and (bonding adj pad)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:43
8	3	(174/250-268.ccls. and (bonding adj pad)) and (polysilicon)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:44
9	3	((174/250-268.ccls. and (bonding adj pad)) and (polysilicon)) and thickness	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:44
10	3	("5045918"   "5124781"   "5394013").PN.	USPAT	2003/02/12 15:37
11	4	5723822.URPN.	USPAT	2003/02/12 15:41
12	305	361/760-803.ccls. and (bonding adj pad)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:48
13	15	(361/760-803.ccls. and (bonding adj pad)) and (polysilicon)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:44
14	8	((361/760-803.ccls. and (bonding adj pad)) and (polysilicon)) and thickness	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:49
15	3819	257/\$.ccls. and (bonding adj pad)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 15:48
16	27	(257/\$.ccls. and (bonding adj pad)) and (thickness near polysilicon)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 16:21
17	36	(257/\$.ccls. and (bonding adj pad)) and (thickness near (metal adj layer))	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 16:54

18	682	(257/\$.ccls. and (bonding adj pad)) and (metal adj layer)	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 16:33
19	523	((257/\$.ccls. and (bonding adj pad)) and (metal adj layer)) and thickness	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 16:33
20	18	(257/\$.ccls. and (bonding adj pad)) and (thickness adj (metal adj layer))	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 16:34
21	3	(361/760-803.ccls. and (bonding adj pad)) and (thickness near (metal adj layer))	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 16:59
22	1	(361/760-803.ccls. and (bonding adj pad)) and (thickness near (dielectric adj layer))	USPAT; EPO; JPO; DERWENT; USOCR	2003/02/12 17:00